

Automotive Power



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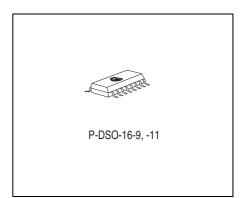


LIN-Transceiver with Voltage Regulator

TLE 6286

Features

- Single-wire transceiver, suitable for **LIN** protocol
- Transmission rate up to 20 kBaud
- Compatible to LIN specification 1.3, 2.0
- Compatible to ISO 9141 functions
- Low current consumption in sleep mode
- Control output for voltage regulator
- LIN bus, short circuit proof to ground and battery
- Integrated 5V Low drop voltage regulator
- Output voltage tolerance ≤ ±2%
- 200 mA output current capability
- Watchdog
- Wide temperature range
- Overtemperature protection
- Suitable for use in automotive electronics.



Description

The TLE 6286 is a single-wire transceiver with a 5V voltage regulator. It is a chip-by-chip integrated circuit in a P-DSO-16-11 package. It works as an interface between the protocol controller and the physical bus. The TLE 6286 is especially suitable to drive the bus line in LIN systems in automotive and industrial applications. Further it can be used in standard ISO9141 systems.

To reduce the current consumption the TLE 6286 offers a sleep operation mode. In this setup a voltage regulator can be controlled by the LIN Transceiver to minimize the current consumption of the whole application. The on-chip voltage regulator is designed for this application but it is also possible to use an external voltage regulator. A wake-up caused by a message on the bus enables the voltage regulator and sets the RxD output low until the device is switched to normal operation mode.

The TLE 6286 is designed to withstand the severe conditions of automotive applications.

Туре	Ordering Code	Package
TLE 6286 G	on request	P-DSO-16-11



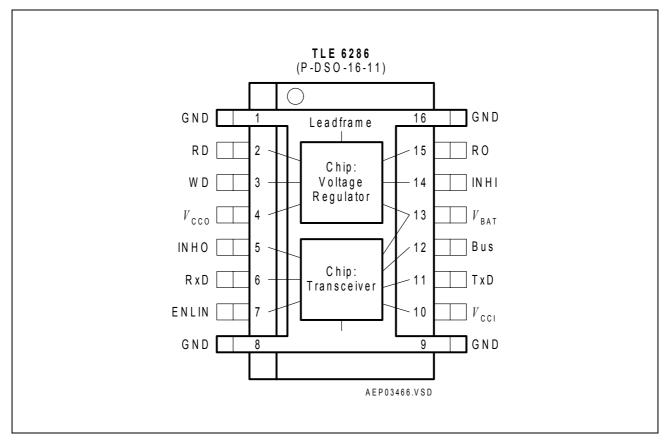


Figure 1 Pin Configuration (top view)



 Table 1
 Pin Definitions and Functions

Pin No.	Symbol	Function
1, 8, 9, 16	GND	Ground; place to cooling tabs to improve thermal behavior
2	RD	Reset delay; connected to ground with external delay capacitor
3	WD	Watchdog; rising-edge triggered, for monitoring a microcontroller
4	V_{cco}	5-V Output ; connected to GND with 22 μ F capacitor, ESR < 3 Ω at 10kHz
5	INHO	Inhibit LIN Output; to control a voltage regulator
6	RxD	Receive Data Output; internal pull-up, LOW in dominate state
7	ENLIN	Enable LIN Input; integrated 30 k Ω pull-down, transceiver in normal operation mode when HIGH
10	V_{CCI}	5-V Supply Input; $V_{\rm CC}$ input to supply the LIN transceiver
11	TxD	Transmit Data Input; internal pull-up, LOW in dominant state
12	BUS	LIN BUS Output/Input ; internal 30 k Ω pull-up to $V_{\rm S}$, LOW in dominant state
13	V_{BAT}	Battery Supply Input; a reverse current protection diode is required, block GND with 100 nF ceramic capacitor and 22 μF capacitor
14	INHI	Inhibit Voltage Regulator Input; TTL compatible, HIGH active input (HIGH switches the VR on); connect to V _{BAT} if not needed
15	RO	Reset Output; open collector output connected to the output via a resistor of 30 $\mbox{k}\Omega$



Functional Block Diagram

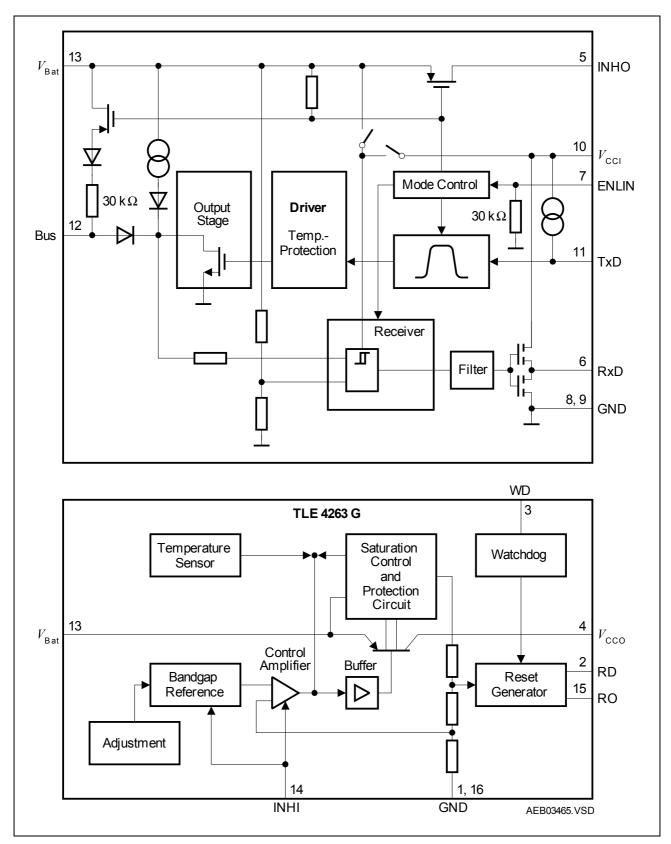


Figure 2 Block Diagram



Circuit Description

The TLE 6286 is a single-wire transceiver combined with a LDO. It is a chip-by-chip integrated circuit in a P-DSO-16-11 package. It works as an interface between the protocol controller and the physical bus. The TLE 6286 is especially suitable to drive the bus line in LIN systems in automotive and industrial applications. Further it can be used in standard ISO9141 systems. The on-chip voltage regulator with watchdog is designed for sleep mode applications but it is also possible to use an external voltage regulator.

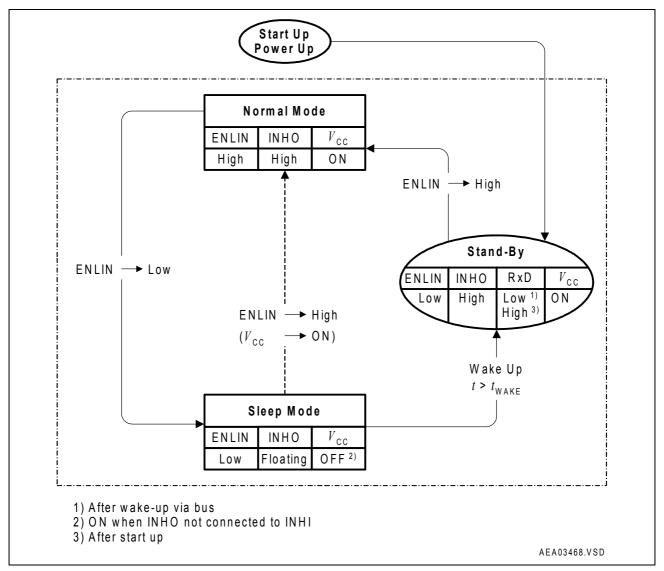


Figure 3 Operation Mode State Diagram

Operation Modes

In order to reduce the current consumption the TLE 6286 offers a sleep operation mode. This mode is selected by switching the enable input ENLIN low (see **Figure 3**, **Operation Mode State Diagram**). In the sleep mode a voltage regulator can be controlled via the INHO output in order to minimize the current consumption of the whole



application. A wake-up caused by a message on the communication bus automatically enables the voltage regulator by switching the INHO output high. In parallel the wake-up is indicated by setting the RxD output low. When entering the normal mode this wake-up flag is reset and the RxD output is released to transmit the bus data.

In case the voltage regulator control input INHI is not connected to INHO output or the microcontroller is active respectively, the TLE 6286 can be set in normal operation mode without a wake-up via the communication bus.

LIN Transceiver

The LIN Transceiver has already a pull-up resistor of 30 k Ω as termination implemented. There is also a diode in this path, to protect the circuit from feedback of voltages from the bus line to the power supply. To configure the TLE 6286 as a master node, an additional external termination resistor of about 1 k Ω is required. To avoid reverse currents from the bus line into the battery supply line in case of an unpowered node, it is also recommended to place a diode in series to the external pull-up. For small systems (low bus capacitance) the EMC performance of the system is supported by an additional capacitor of at least 1 nF in the master node (see **Figure 8**, **Application Example without Bus Short to GND Protection**).

An capacitor of 10 μ F at the supply voltage input $V_{\rm S}$ buffers the input voltage. In combination with the required reverse polarity diode this prevents the device from detecting power down conditions in case of negative transients on the supply line.

Bus Short to GND Feature

The TLE 6286 also has a BUS short to GND feature implemented, in order to protect the battery from running out of charge. A normal master termination connection like described above, 1 k Ω resistor and diode between bus and $V_{\rm S}$, would cause a constantly drawn current via this path. The resulting resistance of this short to GND is lower than 1 k Ω . To avoid this current during a generator off state, like a parked car, the sleep mode has a bus short to GND feature implemented in the TLE 6286. This feature is only applicable, if the master termination is connected with the INHO pin, instead of the $V_{\rm S}$. For a more detailed information see the application circuit in **Figure 8** and **Figure 9**.

Voltage Regulator

The control amplifier compares a reference voltage, which is kept highly accurate by resistance adjustment, to a voltage that is proportional to the output voltage and drives the base of the series transistor via a buffer. Saturation control as a function of the load current prevents any over-saturation of the power element. If the externally scaled down output voltage at the reset threshold input drops below 1.35 V, the external reset delay capacitor is discharged by the reset generator. When the voltage of the capacitor reaches the lower threshold $V_{\rm DRI}$, a reset signal occurs at the reset output and is held



until the upper threshold $V_{\rm DU}$ is exceeded. If the reset threshold input is connected to GND, reset is triggered at an output voltage of typ. 4.65 V. A connected microcontroller will be monitored through the watchdog logic. In case of missing pulses at pin W, the reset output is set to low. The pulse sequence time can be set in a wide range with the reset delay capacitor. The IC can be switched at the TTL-compatible, low-active inhibit input. The IC also incorporates a number of internal circuits for protection against overload, overtemperature, reverse polarity.

Input Capacitor

The input capacitor $C_{\rm I}$ is necessary for compensation of line influences. Using a resistor of approx. 1 Ω in series with $C_{\rm I}$, the oscillating circuit consisting of input inductivity and input capacitance can be damped. The output capacitor is necessary for the stability of the regulating circuit. Stability is guaranteed at values \geq 22 μ F and an ESR < 3 Ω at 10kHz within the operating temperature range. For small tolerances of the reset delay the spread of the capacitance of the delay capacitor and its temperature coefficient should be noted.

Reset Timing

The power-on reset delay time is defined by the charging time of an external capacitor C_D which can be calculated as follows:

$$C_{\rm D} = (t_{\rm rd} \times I_{\rm D.ch}) / \Delta V \tag{1}$$

Definitions:

- C_D = delay capacitor
- t_{rd} = reset delay time
- $I_{D.ch}$ = charge current, typical 60 μ A
- $\Delta V = V_{\text{DH}}$, typical 1.70 V
- V_{DU} = upper delay switching threshold at C_D for reset delay time



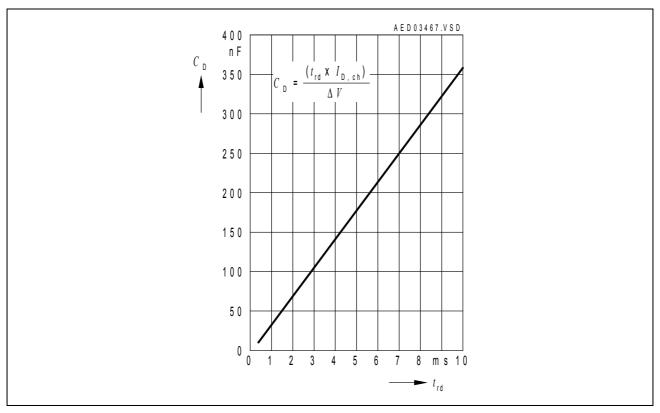


Figure 4 Typical Reset Delay Timing vs. Delay Capacitance

The reset reaction time $t_{\rm rr}$ is the time it takes the voltage regulator to set the reset out LOW after the output voltage has dropped below the reset threshold. It is typically 1 μ s for delay capacitor of 47 nF. For other values for $C_{\rm D}$ the reaction time can be estimated using the following equation:

$$t_{\rm rr} \approx 20 \text{ s/F} \times C_{\rm D}$$
 (2)

For the reset timing diagram please refer to Figure 6.

Watchdog Timing

The frequency of the watchdog pulses has to be higher than the minimum pulse sequence which is set by the external reset delay capacitor $C_{\rm D}$. Calculation can be done according to the formulas given in **Figure 5**. For the watchdog timing diagram please refer to **Figure 7**.

$$T_{\text{Wl.tr}} = \left[\left(V_{\text{DU}} \times V_{\text{DWL}} \right) / I_{\text{D.wd}} \right] / C_{\text{D}}$$
(3)

Definitions:

- T_{WI tr} = watchdog trigger time
- $I_{D.wd}$ = discharge current, typical 6.25 μ A
- $V_{\rm DWL}$ = lower timing threshold



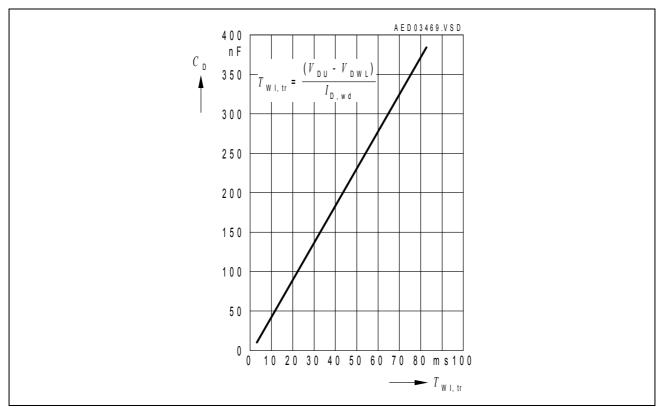


Figure 5 Typical Watchdog Trigger Time vs. Delay Capacitance

Please note that in all calculations with capacitances, the leakage current of the capacitor is neglected!



 Table 2
 Absolute Maximum Ratings

Parameter	Symbol	Limi	t Values	Unit	Remarks
		Min.	Max.		
Voltages	1		-		
Supply voltage	V_{CCI}	-0.3	6	V	_
Battery supply voltage	V_{BAT}	-0.3	40	٧	_
Bus input voltage	V_{bus}	-20	32	٧	_
Bus input voltage	V_{bus}	-20	40	V	t < 1 s
Logic voltages at ENLIN, TxD, RxD	V_{I}	-0.3	V _{CC} + 0.3	V	$0 \text{ V} < V_{\text{CC}} < 5.5 \text{ V}$
Input voltages at INHO	V_{INHO}	-0.3	V _S + 0.3	V	_
Output current at INHO	I_{INHO}	_	20	mA	-
Reset output voltage	V_{RO}	-0.3	40	V	_
Reset delay voltage	V_{RD}	-0.3	40	V	_
Output voltage $V_{\rm CCO}$	$V_{\sf CCO}$	-0.3	7	V	_
INHI voltage	V_{INHI}	-40	40	V	_
Watchdog voltage	V_{WD}	-0.3	6	V	_
Electrostatic discharge voltage at $V_{\rm S}$, Bus vs. GND	V_{ESD}	-4	4	kV	human body model (100 pF via 1.5 k Ω)
Electrostatic discharge voltage	V_{ESD}	-2	2	kV	human body model (100 pF via 1.5 k Ω)
Temperatures		•	•		
Junction temperature	T_{i}	-40	150	°C	_

Note: Maximum ratings are absolute ratings; exceeding any one of these values may cause irreversible damage to the integrated circuit.



Table 3 Operating Range

Parameter	Symbol	Li	mit Valu	es	Unit	Remarks
		Min.	Тур.	Max.		
Supply voltage	V_{CCI}	4.5	_	5.5	٧	_
Battery Supply voltage	V_{BAT}	6	_	35	٧	_
Junction temperature	T_{j}	-40	_	150	°C	_
Thermal Shutdown (june	ction tem	perature)			
Thermal shutdown temp.	T_{jSD}	150	170	190	°C	_
Thermal shutdown hyst.	ΔT	_	10	_	K	_
Thermal Resistances						
Junction ambient	$R_{ ext{thj-a}}$	_	80	_	K/W	PCB heat sink area 300mm ²



Table 4 Electrical Characteristics

Parameter	Sym-	Lir	nit Valı	ues	Unit	Remarks
	bol	Min.	Тур.	Max.		
Current Consumption		1		•		
	I_{BAT}	_	1.5	2.3	mA	recessive state; INHI = INHO = HIGH; $V_{TxD} = V_{CC}$; without R_{L}
	I_{BAT}	_	2.1	3.3	mA	$\begin{aligned} &\text{dominant state;}\\ &\text{INHI} = \text{INHO} = \text{HIGH;}\\ &V_{\text{TxD}} = 0 \text{ V; without } R_{\text{L}} \end{aligned}$
Current consumption V_{CCI} (LIN only)	I_{CCI}	_	0.4	0.7	mA	recessive state; LDO sleep; $V_{\text{TxD}} = V_{\text{CC}}$
	$I_{\rm CCI}$	_	0.4	8.0	mA	dominant state; LDO sleep; $V_{\text{TxD}} = 0 \text{ V}$
Current consumption sleep mode (LIN + voltage regulator)	I_{BAT}	_	20	40	μΑ	sleep mode; INHI = INHO = LOW; $T_{\rm j}$ < 85 °C
(LIN only)	I_{CCI}	_	3	10	μΑ	sleep mode; INHI = INHO = LOW
Current consumption	I_{BAT}	_	900	1300	μΑ	$I_{\rm CCO}$ = 0 mA
LDO (voltage regulator only, LIN in sleep mode)	I_{BAT}	_	10	18	mA	$I_{\rm CCO}$ = 150 mA
only, Life in Sleep mode)	I_{BAT}	_	15	23	mA	$\begin{split} I_{\text{CCO}} &= \text{150 mA;} \\ V_{\text{BAT}} &= \text{4.5V} \end{split}$
Enable Input (pin ENLIN	l)					
HIGH level input voltage threshold	$V_{EN,on}$	_	2.8	$0.7 \\ \times V_{\rm CC}$	V	normal mode
LOW level input voltage threshold	$V_{EN,off}$	$\begin{array}{ c c }\hline 0.3\\ \times V_{\rm CC}\\ \end{array}$	2.2	_	V	low power mode
ENLIN input hysteresis	$V_{EN,hys}$	300	600	900	mV	_
ENLIN pull-down resistance	R_{EN}	15	30	60	kΩ	_



Parameter	Sym-	Liı	mit Val	ues	Unit	Remarks
	bol	Min.	Тур.	Max.		
Inhibit Output (pin INHO))	•	II.	II.	ı	
Inhibit R_{ON} resistance	R_{onINHO}	_	65	120	Ω	I_{INHO} = -15 mA
Leakage current	$I_{INHO,lk}$	-5.0	_	5.0	μΑ	sleep mode; $V_{\rm INHO}$ = 0 V
$\overline{V_{\sf CC}}$ Output (pin $V_{\sf CCO}$)						
Output voltage	V_{CCO}	4.90	5.00	5.10	V	
Output voltage	V_{cco}	4.90	5.00	5.10	V	
Output current	$I_{\sf CCO}$	200	250	400	mA	1)
Drop voltage	V_{dr}	_	0.35	0.50	V	$I_{\rm CCO} = 150 \; {\rm mA}^{1)}$
Load regulation	$\Delta V_{CCO,lo}$	_	_	25	mV	$I_{\rm CCO}$ = 5 mA to 150 mA
Line regulation	$\Delta V_{ m CCO,li}$	_	3	25	mV	$V_{\rm BAT}$ = 6 V to 28 V; $I_{\rm CCO}$ = 150 mA
Power Supply Ripple Rejection	PSRR	_	54	_	dB	$^{2)} f_{\rm r}$ = 100 Hz; $V_{\rm r}$ = 0.5 Vpp
Reset Generator (pin Ri	D)	•	1	1	1	
Switching threshold	$V_{Q,rt}$	4.5	4.65	4.8	V	-
Reset low voltage	$V_{RO,I}$	_	0.10	0.40	V	$I_{\rm RO}$ = 1 mA
Saturation voltage	$V_{D,sat}$	_	50	100	mV	$V_{\rm Q} < V_{\rm R,th}$
Upper timing threshold	V_{DU}	1.45	1.70	2.05	V	_
Lower reset timing threshold	V_{DRL}	0.20	0.35	0.55	V	_
Charge current	$I_{D,ch}$	40	60	85	μΑ	_
Reset delay time	$t_{\rm rd}$	1.3	2.8	4.1	ms	$C_{\rm D}$ = 100 nF
Reset reaction time	$t_{\rm rr}$	0.5	1.2	4	μs	$C_{\rm D}$ = 100 nF



Parameter	Sym-	Lir	nit Valu	ıes	Unit	Remarks
	bol	Min.	Тур.	Max.		
Watchdog (pin WD)						
Discharge current	$I_{D,wd}$	4.40	6.25	9.10	μΑ	$V_{\rm D}$ = 1.0 V
Upper timing threshold	V_{DU}	1.45	1.70	2.05	V	_
Lower timing threshold	V_{DWL}	0.20	0.35	0.55	V	_
Watchdog trigger time	$T_{WI,tr}$	16	22.5	27	ms	$C_{\rm D}$ = 100 nF
Inhibit Input (INHI)						
Switching voltage	$V_{INHI,ON}$	3.6	_	_	V	IC turned on
Turn-OFF voltage	$V_{INHI,OFF}$	_	_	0.8	V	IC turned off
Input current	I_{INHI}	5	10	25	μΑ	$V_{INHI} = 5 \; V$
Receiver Output RxD			<u> </u>	ı	I	
HIGH level output current	$I_{RxD,H}$	-1.2	-0.8	-0.5	mA	$V_{RxD} = 0.8 \times V_{CC}$
LOW level output current	$I_{RxD,L}$	0.5	0.8	1.2	mA	$V_{RxD} = 0.2 \times V_{CC}$
Transmission Input TxD						
HIGH level input voltage threshold	$V_{TxD,H}$	_	2.9	$0.7 \\ \times V_{\rm CC}$	٧	recessive state
TxD input hysteresis	$V_{TxD,hys}$	300	700	900	mV	_
LOW level input voltage threshold	$V_{TxD,L}$	$0.3 \\ \times V_{\rm CC}$	2.1	_	٧	dominant state
TxD pull-up current	I_{TxD}	-150	-110	-70	μΑ	$V_{TxD} < 0.3 \ V_{CC}$



Parameter	Sym-	Li	mit Val	ues	Unit	Remarks
	bol	Min.	Тур.	Max.		
Bus Receiver		I	I	I	I	
Receiver threshold voltage, recessive to dominant edge	$V_{ m bus,rd}$	0.44 × V _S	0.48 × <i>V</i> _S	_	V	-8 V < $V_{\rm bus}$ < $V_{\rm bus,dom}$
Receiver threshold voltage, dominant to recessive edge	$V_{bus,dr}$	_	0.56 × <i>V</i> _S	0.60 × V _S	V	$V_{ m bus,rec} < V_{ m bus} <$ 20 V
Receiver hysteresis	$V_{ m bus,hys}$	0.02 × V _S	0.04 × V _S	0.10 × V _S	mV	$\begin{aligned} V_{\rm bus,hys} &= V_{\rm bus,rec} \text{ -} \\ V_{\rm bus,dom} \end{aligned}$
Receiver threshold center voltage	$V_{ m bus,cnt}$	$0.475 \times V_{\rm S}$	$0.5 imes V_{ m S}$	$0.525 \times V_{\rm S}$		LIN2.0 table 3.1
Input leakage current	$I_{ m bus,lek}$	-1			mA	$V_{\rm bus}$ = 0V, $V_{\rm bat}$ = 12V, pull-up resistor as specified in LIN2.0
Wake-up threshold voltage	$V_{\sf wake}$	0.40 × V _S	0.50 × <i>V</i> _S	0.60 × <i>V</i> _S	V	_
Bus Transmitter						
Bus recessive output voltage	$V_{ m bus,rec}$	0.9 × V _S	_	V_{S}	V	$V_{TxD} = V_{CC}$
Bus dominant output voltage	$V_{ m bus,dom}$	0	_	2	V	$V_{\text{TxD}} = 0 \text{ V}$ 7.3V <v<sub>S<27V</v<sub>
		0	_	1.2	V	$V_{TxD} = 0 V$ $6V < V_{S} < 7.3V$
Bus short circuit current	$I_{bus,sc}$	40	100	150	mA	$V_{\rm bus,short}$ = 13.5 V
Leakage current	$I_{ m bus,lk}$	-1	-	_	mA	$\begin{split} V_{\mathrm{CC}} &= 0 \text{ V}, \ V_{\mathrm{S}} = 0 \text{ V}, \\ V_{\mathrm{bus}} &= -8 \text{ V}, \end{split}$
		_	10	20	μΑ	$\begin{split} V_{\mathrm{CC}} &= 0 \text{ V}, \\ V_{\mathrm{S}} &= 13.5 \text{V}, \\ V_{\mathrm{bus}} &= 20 \text{ V}, \end{split}$
Bus pull-up resistance	R_{bus}	20	30	47	kΩ	Normal mode



Parameter	Sym-	Li	mit Val	ues	Unit	Remarks
	bol	Min.	Тур.	Max.		
Dynamic Transceiver (Characteri	stics	•	1	•	
Falling edge slew rate	$S_{ m bus(L)}$	-3	-2.0	-1	V/μ s	60% > V_{bus} > 40% 1 μ_{S} < $(\tau = R_{\text{BUS}} \times C_{\text{BUS}})$ < 5 $\mu_{\text{S}}^{3)}$; V_{CC} = 5 V; V_{S} = 13.5 V
Rising edge slew rate	$S_{ m bus(H)}$	1	1.5	3	V/µ s	$40\% < V_{\text{bus}} < 60\%$ 1 μs < (τ = $R_{\text{BUS}} \times C_{\text{BUS}}$) < 5 μs ³ ; V_{CC} = 5 V; V_{S} = 13.5 V
Slope symmetry	$t_{\sf slopesym}$	-5	_	5	μs	$t_{\rm fslope}$ - $t_{\rm rslope}$
Propagation delay TxD LOW to bus	$t_{\sf d(L),T}$	_	1	4	μs	$V_{\rm CC}$ = 5 V
Propagation delay TxD HIGH to bus	$t_{\sf d(H),T}$	_	1	4	μs	$V_{\rm CC}$ = 5 V
Propagation delay bus dominant to RxD LOW	$t_{\sf d(L),R}$	_	1	6	μs	$V_{\rm CC}$ = 5 V; $C_{\rm RxD}$ = 20 pF
Propagation delay bus recessive to RxD HIGH	$t_{\sf d(H),R}$	_	1	6	μs	$V_{\rm CC}$ = 5 V; $C_{\rm RxD}$ = 20 pF
Receiver delay symmetry	t _{sym,R}	-2	_	2	μs	$t_{\text{sym,R}} = t_{\text{d(L),R}} - t_{\text{d(H),R}}$
Transmitter delay symmetry	$t_{sym,T}$	-2	_	2	μs	$t_{\text{sym,T}} = t_{\text{d(L),T}} - t_{\text{d(H),T}}$
Duty cycle D1	t _{duty1}	0.396	_	-		duty cycle $1^{3)}$ $TH_{Rec}(max) = 0.744 \times V_S;$ $TH_{Dom}(max) = 0.581 \times V_S;$ $V_S = 7.0 \dots 18 V;$ $t_{bit} = 50 \ \mu s;$ $D1 = t_{bus_rec(min)}/2 \ t_{bit};$
Duty cycle D2	t _{duty2}	_	_	0.581		duty cycle $2^{3)}$ $TH_{Rec}(max) = 0.422 \times V_S;$ $TH_{Dom}(max) = 0.264 \times V_S$ $V_S = 7.6 \dots 18 \text{ V};$ $t_{bit} = 50 \mu\text{s};$ $D2 = t_{bus_rec(max)}/2 t_{bit};$



 $V_{\rm CC}$ = 5.0 V; $V_{\rm S}$ = 13.5V; $R_{\rm L}$ = 500 Ω ; $V_{\rm EN}$ > $V_{\rm EN,ON}$; -40 °C < $T_{\rm j}$ < 125 °C; all voltages with respect to ground; positive current flowing into pin; unless otherwise specified.

Parameter	Sym-	Lir	nit Valı	ues	Unit	Remarks
	bol	Min.	Тур.	Max.		
Wake-up delay time	t _{wake}	30	100	150	μs	<i>T</i> _j ≤ 125 °C
		_	_	170	μs	$T_{\rm j} \le 150~{\rm ^{\circ}C^{2)}}$
Delay time for change sleep/stand by mode - normal mode	t _{snorm}	_	_	50	μs	_
Delay time for change normal mode - sleep mode	t _{nsleep}	_	_	50	μs	_

¹⁾ Drop voltage = $V_{\rm i}$ - $V_{\rm Q}$ (measured when the output voltage has dropped 100 mV from the nominal value obtained at 6V input).

Note: The reset output is low within the range $V_{\rm Q}$ = 1 V to $V_{\rm Q,rt}$

²⁾ Not subject to production test, specified by design

³⁾ Bus load conditions concerning LIN spec 2.0 $C_{\rm bus}$, $R_{\rm bus}$ = 1 nF, 1 k Ω / 6.8 nF, 660 Ω / 10 nF, 500 Ω



Diagrams

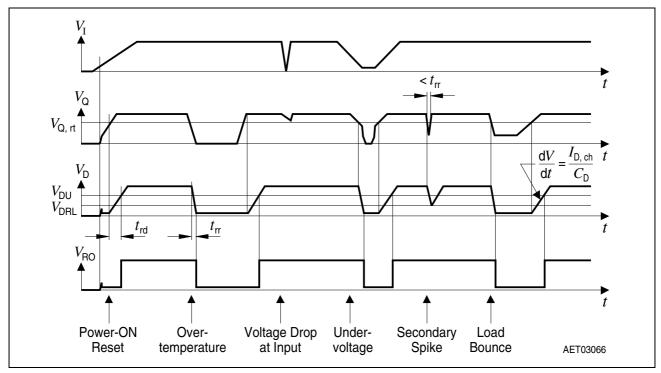


Figure 6 Time Response, Watchdog with High-Frequency Clock

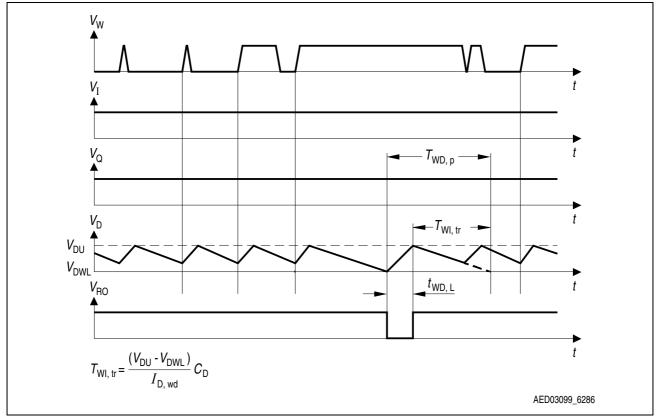


Figure 7 Timing of the Watchdog Function Reset



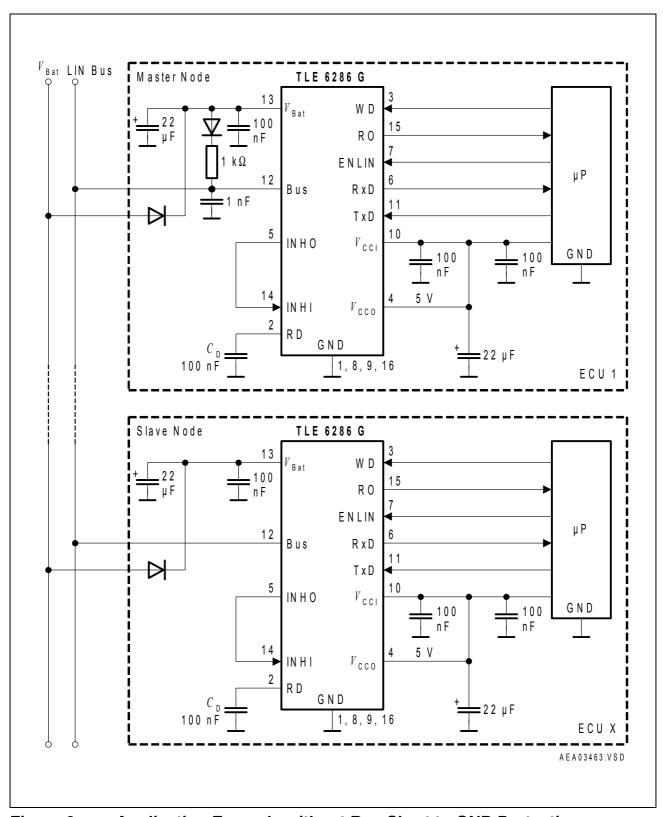


Figure 8 Application Example without Bus Short to GND Protection



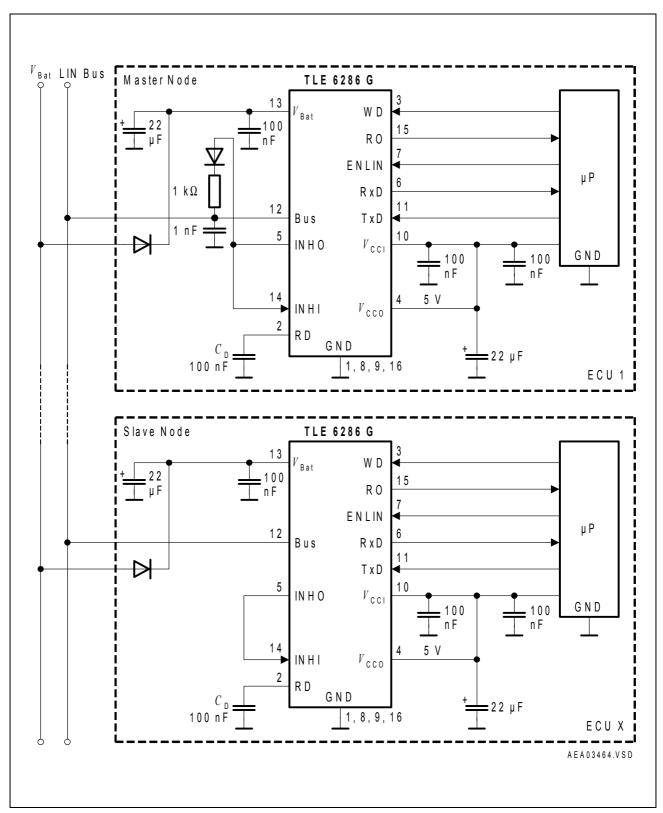


Figure 9 Application Example with Bus Short to GND Protection



Package Outlines

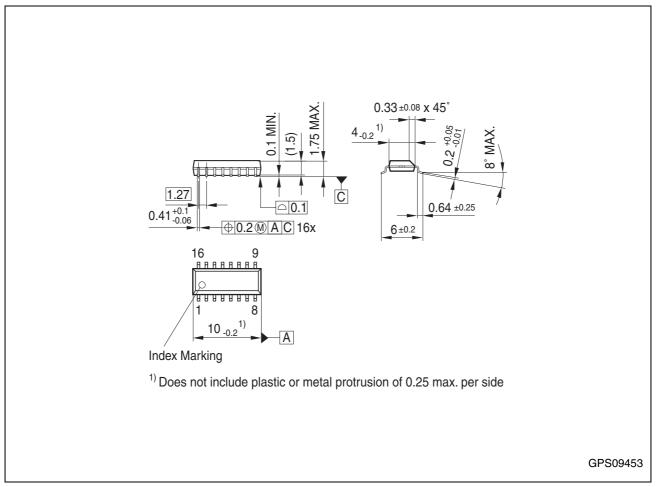


Figure 10 P-DSO-16-11 (Plastic Dual Small Outline)

You can find all of our packages, sorts of packing and others in our Infineon Internet Page "Products": http://www.infineon.com/products.